

Title: Formation of [111]-Ge Domains in layered α -FeGe₂ by MBE and solid phase epitaxy

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Abstract

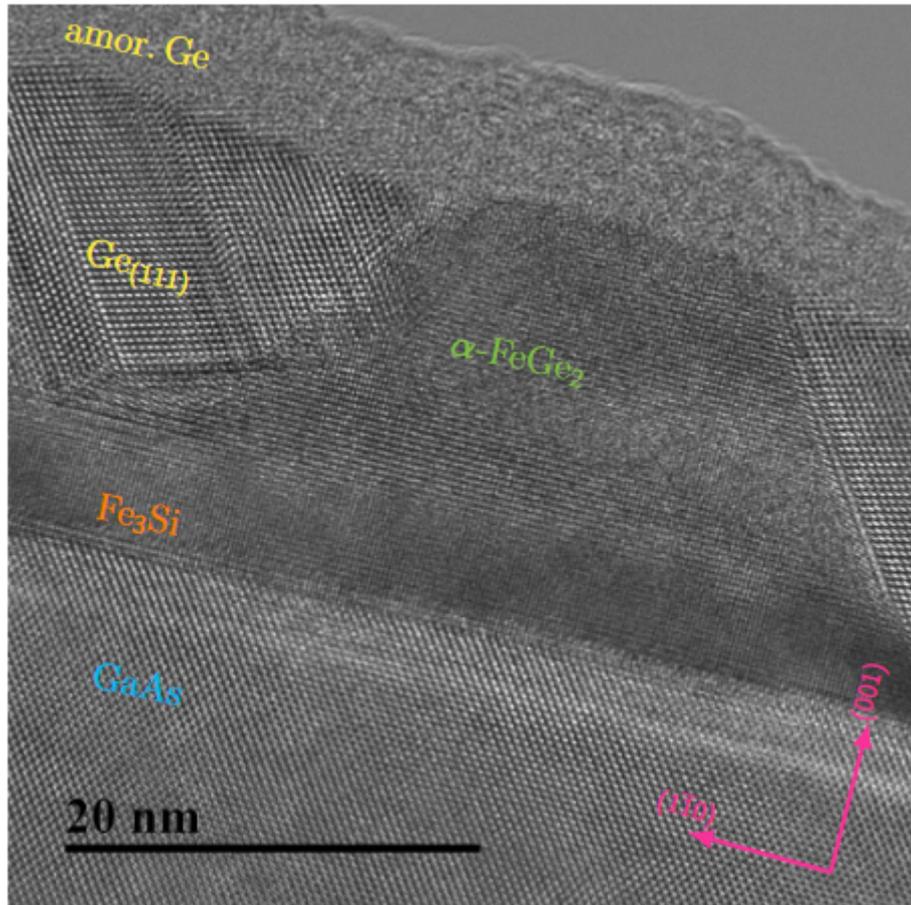


Figure 1: TEM micrograph of α -FeGe₂-layer taken along the [110] zone axis, showing a layer with 15 nm nominal thickness. The α -FeGe₂ is broken up by [111]-Ge domains.